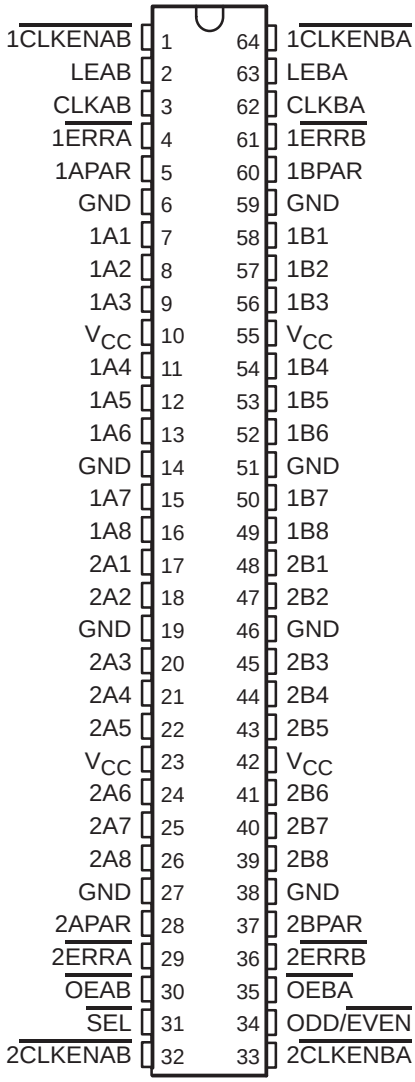
- **Member of the Texas Instruments *Widebus+*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **Simultaneously Generates and Checks Parity**
- **Option to Select Generate Parity and Check or Feed-Through Data/Parity in A-to-B or B-to-A Directions**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Packaged in Thin Shrink Small-Outline Package**

DGG PACKAGE
(TOP VIEW)



description

This 18-bit (dual-octal) noninverting registered transceiver is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74ALVCH16901 is a dual 9-bit to dual 9-bit parity transceiver with registers. The device can operate as a feed-through transceiver or it can generate/check parity from the two 8-bit data buses in either direction.

The SN74ALVCH16901 features independent clock (CLKAB or CLKBA), latch-enable (LEAB or LEBA), and dual 9-bit clock-enable ($\overline{\text{CLKENAB}}$ or $\overline{\text{CLKENBA}}$) inputs. It also provides parity-enable ($\overline{\text{SEL}}$) and parity-select (ODD/$\overline{\text{EVEN}}$) inputs and separate error-signal ($\overline{\text{ERRA}}$ or $\overline{\text{ERRB}}$) outputs for checking parity. The direction of data flow is controlled by $\overline{\text{OEAB}}$ and $\overline{\text{OEBA}}$. When $\overline{\text{SEL}}$ is low, the parity functions are enabled. When $\overline{\text{SEL}}$ is high, the parity functions are disabled and the device acts as an 18-bit registered transceiver.

To ensure the high-impedance state during power up or power down, $\overline{\text{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16901 is characterized for operation from –40°C to 85°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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Function Tables

FUNCTION†

INPUTS					OUTPUT
$\overline{\text{CLKENAB}}$	$\overline{\text{OEAB}}$	LEAB	CLKAB	A	B
X	H	X	X	X	Z
X	L	H	X	L	L
X	L	H	X	H	H
H	L	L	X	X	B_0‡
L	L	L	↑	L	L
L	L	L	↑	H	H
L	L	L	L	X	B_0‡
L	L	L	H	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar, but uses $\overline{\text{OEBA}}$, LEBA, and $\overline{\text{CLKENBA}}$.
‡ Output level before the indicated steady-state input conditions were established
§ Output level before the indicated steady-state input conditions were established, provided that CLKAB was low before LEAB went low

PARITY ENABLE

INPUTS			OPERATION OR FUNCTION	
$\overline{\text{SEL}}$	$\overline{\text{OEBA}}$	$\overline{\text{OEAB}}$		
L	H	L	Parity is checked on port A and is generated on port B.	
L	L	H	Parity is checked on port B and is generated on port A.	
L	H	H	Parity is checked on port B and port A.	
L	L	L	Parity is generated on port A and B if device is in FF mode.	
H	L	L	Parity functions are disabled; device acts as a standard 18-bit registered transceiver.	Q_A data to B, Q_B data to A
H	L	H		Q_B data to A
H	H	L		Q_A data to B
H	H	H		Isolation

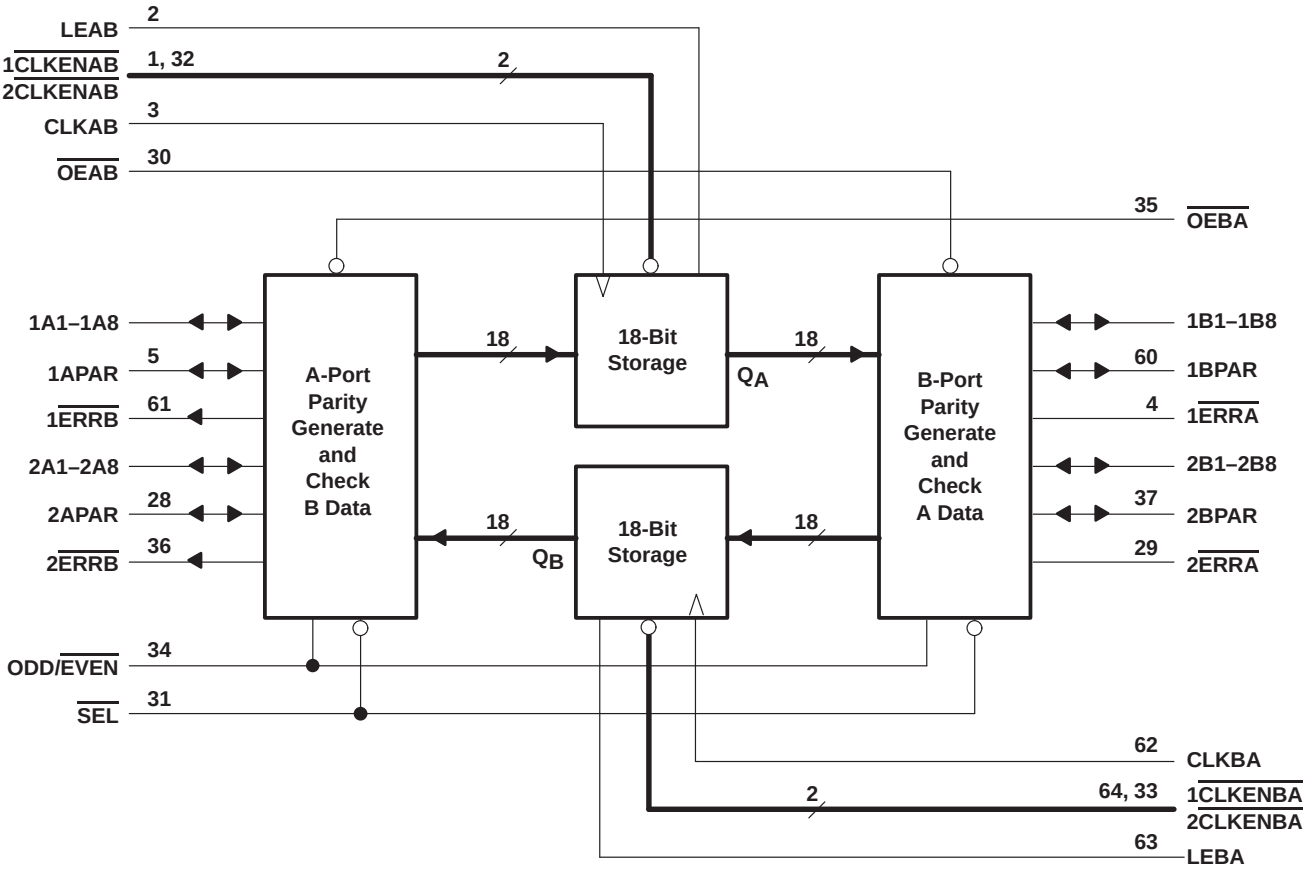
Function Tables (Continued)

PARITY

INPUTS								OUTPUTS			
$\overline{SEL}$	$\overline{OEBA}$	$\overline{OEAB}$	ODD/$\overline{EVEN}$	Σ OF INPUTS A1–A8 = H	Σ OF INPUTS B1–B8 = H	APAR	BPAR	APAR	$\overline{ERRA}$	BPAR	$\overline{ERRB}$
L	H	L	L	0, 2, 4, 6, 8	N/A	L	N/A	N/A	H	L	Z
L	H	L	L	1, 3, 5, 7	N/A	L	N/A	N/A	L	H	Z
L	H	L	L	0, 2, 4, 6, 8	N/A	H	N/A	N/A	L	L	Z
L	H	L	L	1, 3, 5, 7	N/A	H	N/A	N/A	H	H	Z
L	L	H	L	N/A	0, 2, 4, 6, 8	N/A	L	L	Z	N/A	H
L	L	H	L	N/A	1, 3, 5, 7	N/A	L	H	Z	N/A	L
L	L	H	L	N/A	0, 2, 4, 6, 8	N/A	H	L	Z	N/A	L
L	L	H	L	N/A	1, 3, 5, 7	N/A	H	H	Z	N/A	H
L	H	L	H	0, 2, 4, 6, 8	N/A	L	N/A	N/A	L	H	Z
L	H	L	H	1, 3, 5, 7	N/A	L	N/A	N/A	H	L	Z
L	H	L	H	0, 2, 4, 6, 8	N/A	H	N/A	N/A	H	H	Z
L	H	L	H	1, 3, 5, 7	N/A	H	N/A	N/A	L	L	Z
L	L	H	H	N/A	0, 2, 4, 6, 8	N/A	L	H	Z	N/A	L
L	L	H	H	N/A	1, 3, 5, 7	N/A	L	L	Z	N/A	H
L	L	H	H	N/A	0, 2, 4, 6, 8	N/A	H	H	Z	N/A	H
L	L	H	H	N/A	1, 3, 5, 7	N/A	H	L	Z	N/A	L
L	H	H	L	0, 2, 4, 6, 8	0, 2, 4, 6, 8	L	L	Z	H	Z	H
L	H	H	L	1, 3, 5, 7	1, 3, 5, 7	L	L	Z	L	Z	L
L	H	H	L	0, 2, 4, 6, 8	0, 2, 4, 6, 8	H	H	Z	L	Z	L
L	H	H	L	1, 3, 5, 7	1, 3, 5, 7	H	H	Z	H	Z	H
L	H	H	H	0, 2, 4, 6, 8	0, 2, 4, 6, 8	L	L	Z	L	Z	L
L	H	H	H	1, 3, 5, 7	1, 3, 5, 7	L	L	Z	H	Z	H
L	H	H	H	0, 2, 4, 6, 8	0, 2, 4, 6, 8	H	H	Z	H	Z	H
L	H	H	H	1, 3, 5, 7	1, 3, 5, 7	H	H	Z	L	Z	L
L	L	L	L	N/A	N/A	N/A	N/A	PE†	Z	PE†	Z
L	L	L	H	N/A	N/A	N/A	N/A	PO‡	Z	PO‡	Z

† Parity output is set to the level so that the specific bus side is set to even parity.
‡ Parity output is set to the level so that the specific bus side is set to odd parity.

functional block diagram



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I: Except I/O ports (see Note 1) . . . . . –0.5 V to 4.6 V
I/O ports (see Notes 1 and 2 . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Continuous output current, I_O . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3) . . . . . 73°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed..
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		1.65	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		$0.35 \times V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	V_{CC}	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–12	
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		12	
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate			10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		1.65 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA		1.65 V	1.2			
		I_{OH} = –6 mA		2.3 V	2			
		I_{OH} = –12 mA		2.3 V	1.7			
				2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2			
V_{OL}		I_{OL} = 100 μA		1.65 V to 3.6 V			0.2	V
		I_{OL} = 4 mA		1.65 V			0.45	
		I_{OL} = 6 mA		2.3 V			0.4	
		I_{OL} = 12 mA		2.3 V			0.7	
				2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I		$V_I = V_{CC}$ or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.58 V		1.65 V	25			μA
		V_I = 1.07 V		1.65 V	–25			
		V_I = 0.7 V		2.3 V	45			
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OZ}§		$V_O = V_{CC}$ or GND		3.6 V			±10	μA
I_{CC}		$V_I = V_{CC}$ or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} – 0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	$V_I = V_{CC}$ or GND		3.3 V		3		pF
C_{io}	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		7.5		pF
C_o	$\overline{ERR}$ ports	$V_O = V_{CC}$ or GND		3.3 V		6		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

			V_{CC} = 1.8 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			†		125		125		125	MHz
t_w	Pulse duration	CLK↑	†		3		3		3		ns
		LE high	†		3		3		3		
t_{su}	Setup time	A, APAR or B, BPAR before CLK↑	†		1.9		2		1.7		ns
		$\overline{\text{CLKEN}}$ before CLK↑	†		2.1		2.1		1.7		
		A, APAR or B, BPAR before LE↓	†		1.4		1.3		1.2		
t_h	Hold time	A, APAR or B, BPAR after CLK↑	†		0.4		0.4		0.5		ns
		$\overline{\text{CLKEN}}$ after CLK↑	†		0.5		0.5		0.7		
		A, APAR or B, BPAR after LE↓	†		0.9		1.1		0.9		

† This information was not available at the time of publication.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.8 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			†		125		125		125		MHz
t_{pd}	A or B	B or A		†	1	5.2		4.8	1	4.4	ns
		BPAR or APAR		†	2	8.9		7.6	2	6.7	
	APAR or BPAR	BPAR or APAR		†	1	5.7		5.2	1	4.7	
		$\overline{ERRA}$ or $\overline{ERRB}$		†	2	9.7		8.7	2	7.5	
	ODD/$\overline{EVEN}$	$\overline{ERRA}$ or $\overline{ERRB}$		†	1.5	8.7		7.9	1.5	6.8	
		BPAR or APAR		†	1.5	8.3		7.6	1.5	6.5	
	$\overline{SEL}$	BPAR or APAR		†	1	6.1		5.9	1	5.1	
	CLKAB or CLKBA	A or B		†	1	6.4		5.8	1	5.1	
		BPAR or APAR parity feedthrough		†	1.5	7.1		6.3	1.5	5.6	
		BPAR or APAR parity generated		†	2.5	10.2		8.7	2	7.7	
		$\overline{ERRA}$ or $\overline{ERRB}$		†	2.5	10.5		8.9	2	7.9	
	LEAB or LEBA	A or B		†	1	6		5.5	1	4.8	
		BPAR or APAR parity feedthrough		†	1.5	6.7		6	1.5	5.3	
		BPAR or APAR parity generated		†	2.5	9.8		8.3	2	7.4	
		$\overline{ERRA}$ or $\overline{ERRB}$		†	2.5	9.9		8.5	2	7.5	
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	B, BPAR or A, APAR		†	1.4	6.3		6.1	1	5.3	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	B, BPAR or A, APAR		†	1.3	6.1		5.2	1.5	4.9	ns
t_{en}	$\overline{OEAB}$ or $\overline{OEBA}$	$\overline{ERRA}$ or $\overline{ERRB}$		†	1.4	6.2		5.5	1	4.9	ns
t_{dis}	$\overline{OEAB}$ or $\overline{OEBA}$	$\overline{ERRA}$ or $\overline{ERRB}$		†	1.3	7.3		6.5	1	5.7	ns
t_{en}	$\overline{SEL}$	$\overline{ERRA}$ or $\overline{ERRB}$		†	1.4	6.7		6.5	1	5.5	ns
t_{dis}	$\overline{SEL}$	$\overline{ERRA}$ or $\overline{ERRB}$		†	1.3	6.4		5.4	1.5	4.9	ns

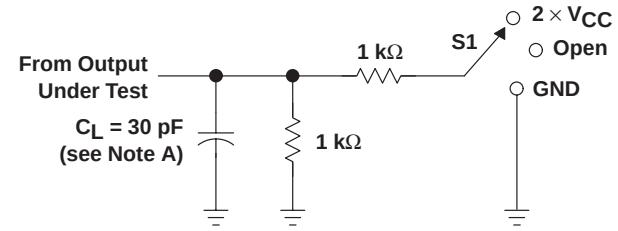
† This information was not available at the time of publication.

operating characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	UNIT
			TYP	TYP	TYP	
C_{pd} Power dissipation capacitance	Outputs enabled	C_L = 50 pF, f = 10 MHz	†	22	27	pF
	Outputs disabled		†	5	8	

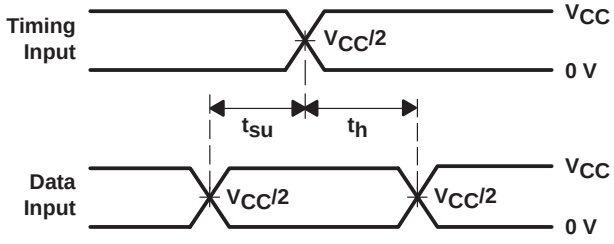
† This information was not available at the time of publication.

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 1.8 V

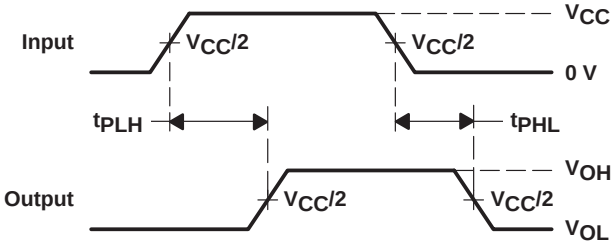


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND

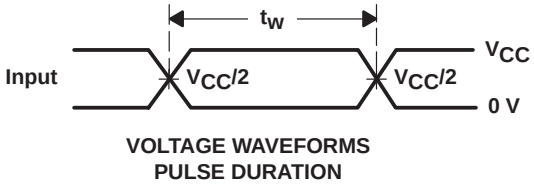
LOAD CIRCUIT



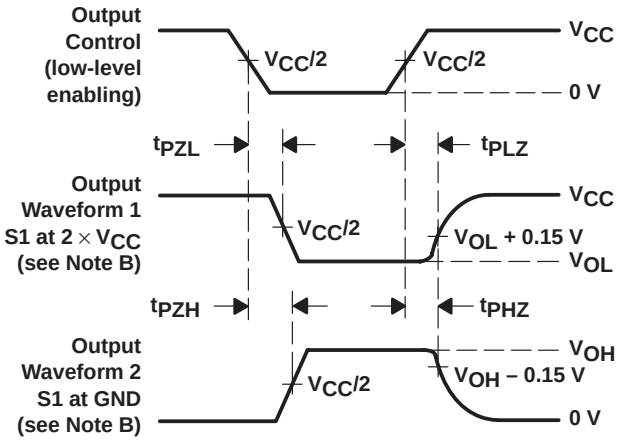
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

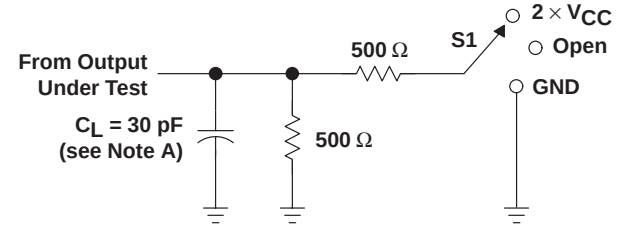


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

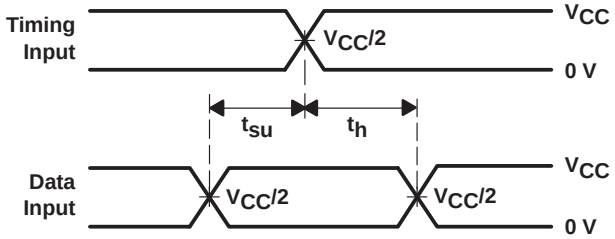
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

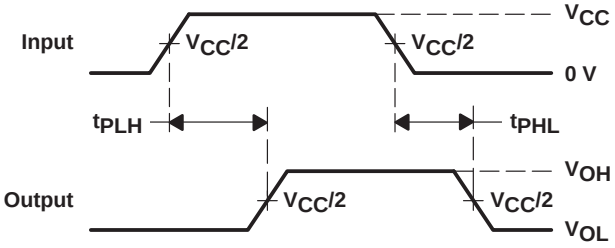


TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 2 × V_{CC} GND

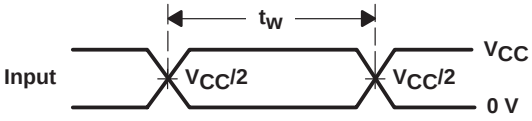
LOAD CIRCUIT



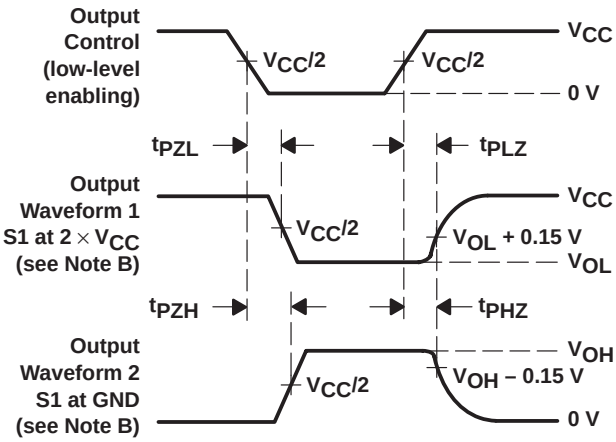
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

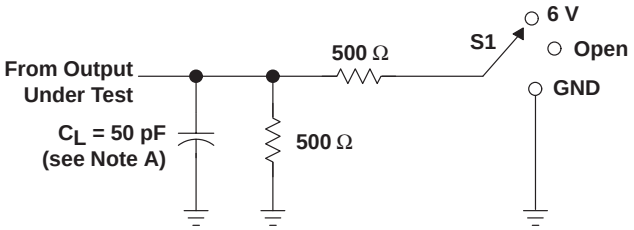


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
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F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

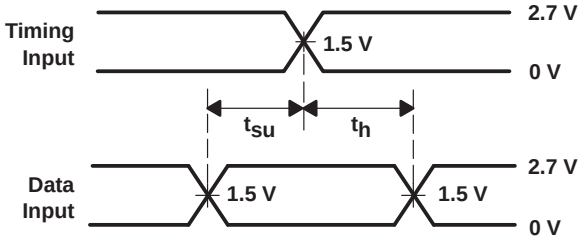
Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

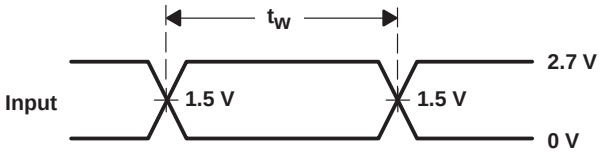


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

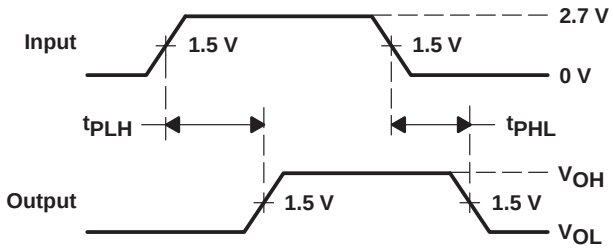
LOAD CIRCUIT



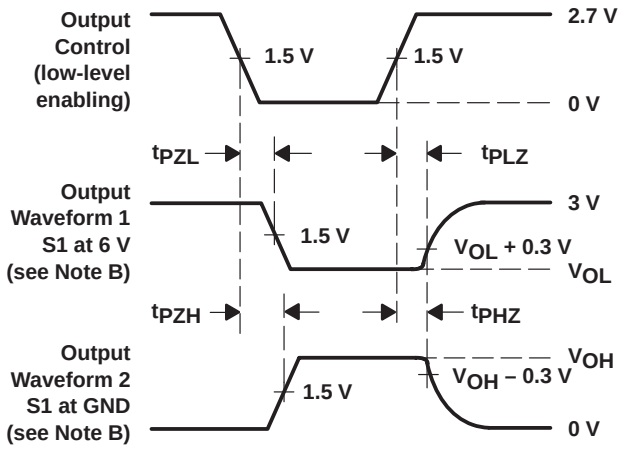
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 3. Load Circuit and Voltage Waveforms

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